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# N-Channel 60 V (D-S) MOSFET

(Pb)
RoHS COMPLIANT

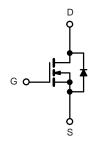
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}$ (m $\Omega$ )(Typ.)	I <sub>D</sub> (A) <sup>a</sup> (Max.)		
60	29 at V <sub>GS</sub> = 10 V	35		
00	36 at $V_{GS} = 4.5 \text{ V}$	35		

#### **FEATURES**

- DT-Trench Power MOSFET
- 100% Rg and UIS Tested

#### **APPLICATIONS**

- Motor Drive
- Power Tools



N-Channel MOSFET

TO-251	Pin Configuration
	Top View



Parameter		Symbol	Limit	Unit
Gate-Source Voltage		V <sub>GS</sub>	± 20	V
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>b</sup>	T <sub>C</sub> = 25 °C	1	35	
	T <sub>C</sub> = 100 °C	l <sub>D</sub>	25 <sup>a</sup>	
Pulsed Drain Current		I <sub>DM</sub>	90	А
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	35	
Avalanche Current		I <sub>AS</sub>	30	
Single Avalanche Energy (Duty Cycle ≤ 1 %)		E <sub>AS</sub>	29	mJ
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	45	W
	T <sub>A</sub> = 25 °C	' D	2.3 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	•	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marian and Irration to Ambianta	t ≤ 10 sec	R <sub>thJA</sub>	13	18	°C/W
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		35	55	
Maximum Junction-to-Case		R <sub>thJC</sub>	2.0	3.0	

#### Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c.  $t \le 10 \text{ s}$ .

Rev. 1. 0



Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit
Static			<u> </u>		_	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA 60		V		
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3	V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	μΑ
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	35			Α
Drain-Source On-State Resistance <sup>b</sup>	P	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A		29	36	mΩ
	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$		36	46	11122
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	$V_{DS} = 5 \text{ V}, I_{D} = 20 \text{ A}$		40		S
Dynamic						
Input Capacitance	C <sub>iss</sub>			826		pF
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$		51		
Reverse Transfer Capacitance	C <sub>rss</sub>			43		
Total Gate Charge <sup>c</sup>	$Q_g$			20	30	
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 15 \text{ A}$		1.9		nC
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			4.5		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			13		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 30 \text{ V}, R_{L} = 1.0 \Omega$		46		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D$ =15 A, $V_{GEN}$ = 10 V, $R_g$ = 2.5 Ω		25		ns
Fall Time <sup>c</sup>	t <sub>f</sub>			10		
Source-Drain Diode Ratings and Cha	aracteristics (	T <sub>C</sub> = 25 °C)				
Pulsed Current	I <sub>SM</sub>				90	Α
Diode Forward Voltage	$V_{SD}$	I <sub>F</sub> = 1 A, V <sub>GS</sub> = 0 V		0.6	1.0	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 15 A, di/dt = 500 A/μs		25	50	ns
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = 15 A, di/dt = 500 A/μs		45	100	nC

#### Notes:

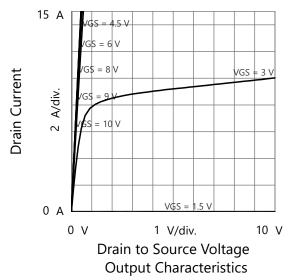
- a. For design aid only; not subject to production testing. b. Pulse test; pulse width  $\,300~\mu s$ , duty cycle  $\,2~\%.$
- c. Independent of operating temperature.

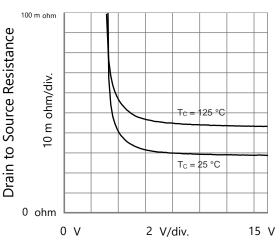
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



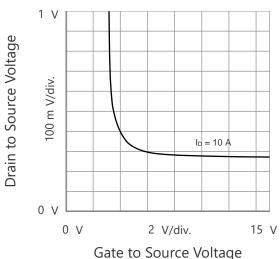


#### TYPICAL CHARACTERISTICS (25 °C unless noted)

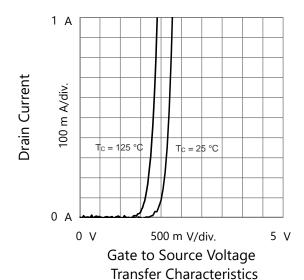


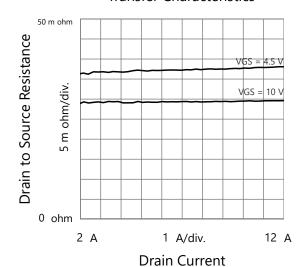


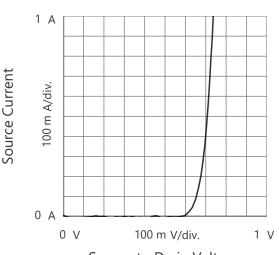
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



Drain to Source Voltage vs. Gate to Source Voltage





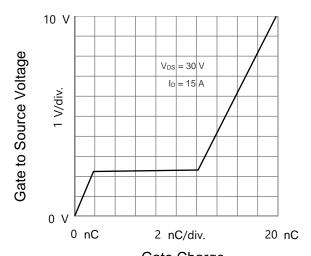


Drain to Source Resistance vs. Drain Current

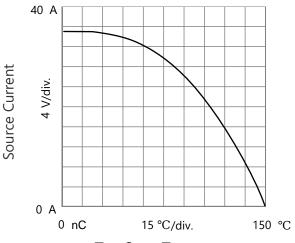
Source to Drain Voltage Body Diode Forward Characteristics



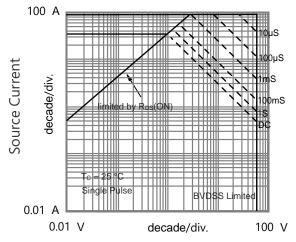
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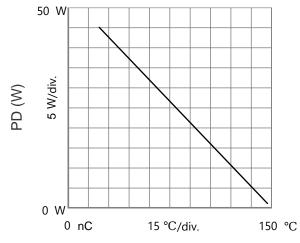
Gate Charge
Gate to Source Voltage vs. GateCharge



 $T_{C} \textbf{ - Case Temperature}_{\text{Current Derating}}$ 



Source to Drain Voltage Safe Operating Area, Junction-to-Ambient

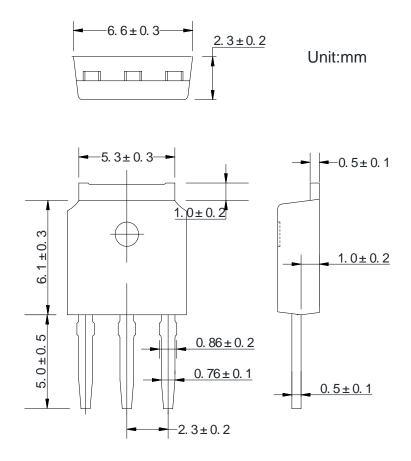


T<sub>C</sub> - Case Temperature

Power Derating



## **TO-251 PACKAGE OUTLINE**





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